2SC2404

Silicon NPN epitaxial planar type

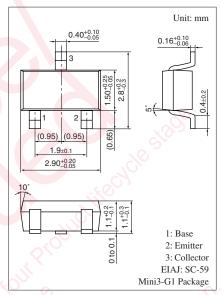
For high-frequency amplification

■ Features

- Optimum for RF amplification of FM/AM radios
- High transition frequency f_T
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V_{CBO} | 30 | V | |
| Collector-emitter voltage (Base open) | V_{CEO} | 20 | V | |
| Emitter-base voltage (Collector open) | V_{EBO} | 3 | V | |
| Collector current | I_{C} | 15 | mA | |
| Collector power dissipation | P_{C} | 150 | mW | |
| Junction temperature | T _j | 150 | °C | |
| Storage temperature | T _{stg} | -55 to +150 | °C | |



Marking Symbol: U

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

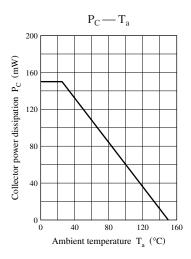
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|------------------|--|-----|------|-----|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_C = 10 \mu\text{A}, I_E = 0$ | 30 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \mu\text{A}, I_C = 0$ | 3 | | | V |
| Base-emitter voltage | V_{BE} | $V_{CB} = 6 \text{ V}, I_{E} = -1 \text{ mA}$ | 1.9 | 0.72 | | V |
| Forward current transfer ratio * | h_{FE} | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}$ | 65 | | 260 | _ |
| Transition frequency | f_T | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$ | 450 | 650 | | MHz |
| Reverse transfer capacitance (Common emitter) | C _{re} | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$ | | 0.8 | 1.0 | pF |
| Power gain | G _P | $V_{CB} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 100 \text{ MHz}$ | | 24 | | dB |
| | - | CB / E | | | | |
| Noise figure | NF | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$ | | 3.3 | | dB |

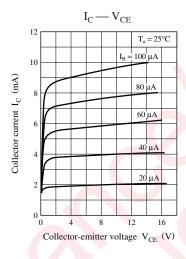
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

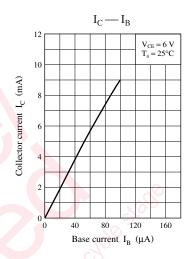
2. *: Rank classification

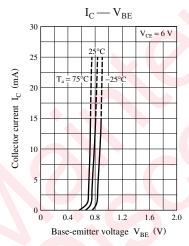
| Rank | С | D |
|----------|-----------|------------|
| h_{FE} | 65 to 160 | 100 to 260 |

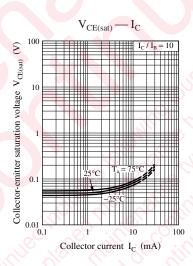
Panasonic

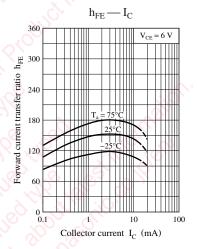


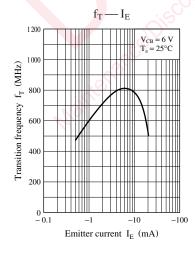


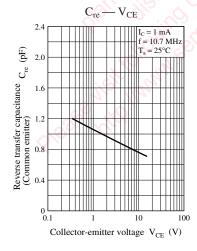


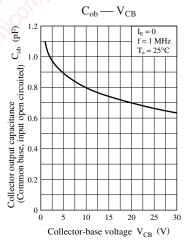




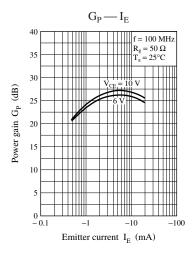


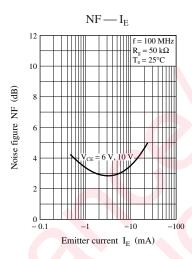


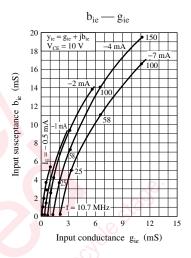


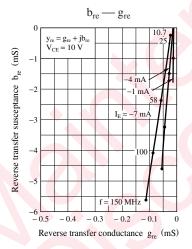


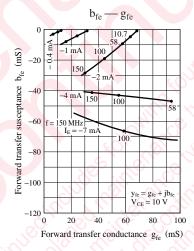
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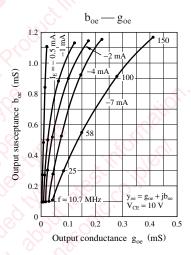












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